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(71) Applicant (for all designated States except US): **WRIOTA PTY LTD** [AU/AU]; c/- Allen and Buckridge, 18 Bulletin Place, Sydney, NSW 2000 (AU).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **WILLIAMS, James, Stanislav** [AU/AU]; 15 Twynam Street, Holder, Australian Capital Territory 2611 (AU). **BRADBY, Jodie**,

Elisabeth [AU/AU]; Unit 8, 41 Halford Crescent, Page, Australian Capital Territory 2614 (AU). **SWAIN, Michael, Vincent** [AU/AU]; 24 Robin Avenue, Turrumurra, New South Wales 2074 (AU).

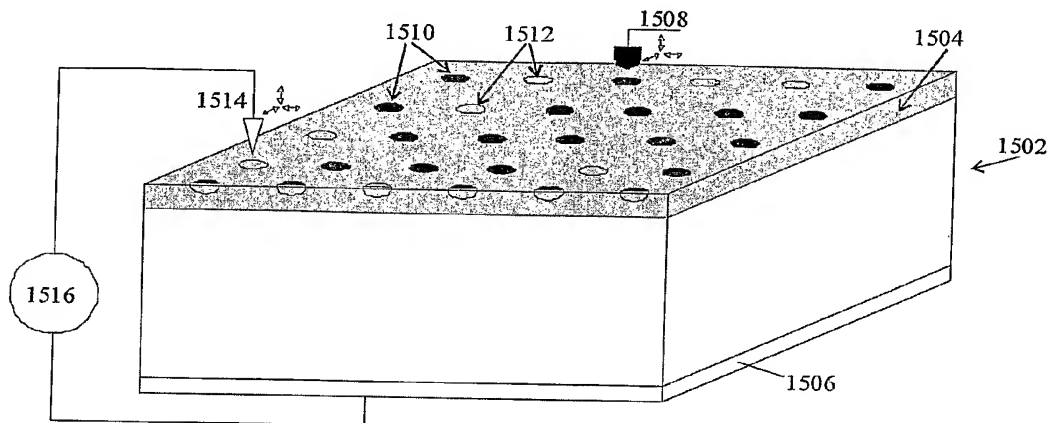
(74) Agents: **WEBBER, David, Brian** et al.; Davies Collison Cave, 1 Nicholson Street, Melbourne, Victoria 3000 (AU).

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(54) Title: A MEMORY DEVICE, AN INFORMATION STORAGE PROCESS, A PROCESS, AND A STRUCTURED MATERIAL



(57) Abstract: A memory device, including a plurality of nanoscale memory cells (1510, 1512) created by applying pressure to and removing pressure from one or more regions (1510, 1512) of a substance (1502) to change the electrical conductivity of those regions (1510, 1512). An electrically conductive read probe (1514) determines the conductivities of the regions and thereby the information stored in the cells. A write probe (1508) applies pressure to and removes pressure from selected cells to change the electrical conductivity of those cells and thereby store or erase information.

WO 2005/057582 A1



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